

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

46. (Amended) A semiconductor device comprising:

a semiconductor chip having a main surface, a back surface and a plurality of side surfaces;

a plurality of electrodes arranged in a plurality of lines on the main surface of the semiconductor chip:

a base resin film formed on the main surface of the semiconductor chip, the base resin film having a first surface facing the main surface of the semiconductor chip, a second surface opposite to the first surface and a through hole provided thereof;

a plurality of conductive patterns formed on the first surface of the base resin film, the conductive patterns extending near the through hole; and

an insulating film formed on the first surface of the base resin film and the conductive patterns, the insulating film having a plurality of electrode holes for exposing a part of the conductive patterns ~~through the through holes~~

a plurality of inner leads connecting the electrodes with the conductive patterns through the through holes.

47. (Previously presented) A semiconductor device according to claim 46, wherein the main surface and side surface of the semiconductor chip are covered by molding resin.

48. (Previously presented) A semiconductor device according to claim 46, further comprising a plurality of solder balls formed on the electrode holes.
49. (Amended) A semiconductor device according to claim 46, wherein the base resin film is formed on the main surface, back surface and side ~~surface~~ surfaces of the semiconductor chip.
50. (Previously presented) A semiconductor device according to claim 46, wherein the base resin film is covered by elastic resin.
51. (Previously presented) A semiconductor device according to claim 50, wherein the elastic resin is polyimide.
52. (Amended) A semiconductor device comprising:
a semiconductor chip having a main surface, a back surface and a plurality of side surfaces;
a plurality of electrodes arranged in a plurality of lines on the main surface of the semiconductor chip;
a base resin film formed on the main surface of the semiconductor chip, the base resin film having a first surface facing said semiconductor chip, a second surface opposite to the first surface and a through hole provided thereof;
~~a plurality of conductive patterns formed on the second surface opposite the first surface and a through hole provided thereof;~~

a plurality of conductive patterns formed on the second surface of the base resin film, the conductive patterns extending near the through hole;
an insulating film formed on the second surface of the base resin film and conductive patterns, the insulating film having a plurality of ~~electrodes~~ electrode holes for exposing a part of the conductive patterns; and
a plurality of inner leads connecting the electrodes with the conductive patterns through the through holes.

53. (Previously presented) A semiconductor device according to claim 52, wherein the main surface and side surface of the semiconductor chip are covered by molding resin.

54. (Amended) A semiconductor device according to claim 52, further comprising a plurality of solder balls formed on the electrodes holes.

55. (Previously presented) A semiconductor device according to claim 52, wherein the base resin film is formed on the main surface, back surface and the side surfaces of the semiconductor chip.

56. (Previously presented) A semiconductor device according to claim 52, wherein the base resin film is covered by elastic resin.

57. (Previously presented) A semiconductor device according to claim 56, wherein the elastic resin is polyimide.

58. (Amended) A semiconductor device comprising:
a semiconductor chip having a main surface, a back surface and a plurality of side surfaces;
a plurality of electrodes arranged in a plurality of lines on the main surface of the semiconductor chip;
a base resin film formed on the main surface of the semiconductor chip, the base resin film having a first surface facing said semiconductor chip and a second surface opposite the first surface;
a plurality of electrode patterns formed on the first surface of the base resin film;
a first insulating film formed on the first surface of the base resin film, the first insulating film having a plurality of first electrode holes for exposing the electrode patterns;
a plurality of conductive patterns formed on the second surface of the base resin film, the conductive patterns electrically connected to the electrode patterns; and
a second insulating film formed on the second surface of the base resin film and the conductive patterns, the insulating film having a plurality of second electrode holes for exposing a part of the conductive patterns.

59. (Previously presented) A semiconductor device according to claim 58, wherein the main surface and the side surface of the semiconductor chip are covered by molding resin.

60. (Previously presented) A semiconductor device according to claim 58, further comprising a plurality of solder balls formed on the second electrodes holes.

61. (Previously presented) A semiconductor device according to claim 58, wherein the base resin film is formed on the main surface, back surface and the side surfaces of the semiconductor chip.

62. (Previously presented) A semiconductor device according to claim 61, wherein the base resin film is substantially surrounding the semiconductor chip.

63. (Previously presented) A semiconductor device according to claim 58, wherein the base resin is covered by elastic resin.

64. (Previously presented) A semiconductor device according to claim 63, wherein the elastic resin is polyimide.